



STL35N6F3

N-channel 60 V, 0.019 Ω , 10 A STripFET™ III Power MOSFET in PowerFLAT™ 5x6 package

Datasheet — production data

Features

Order code	V _{DSS}	R _{DS(on)} max	I _D
STL35N6F3	60 V	< 0.022 Ω	10 A

- N-channel enhancement mode
- 100% avalanche rated
- Low gate charge
- Very low on-resistance

Applications

- Switching applications

Description

This device is an N-channel enhancement mode Power MOSFET produced using STMicroelectronics' STripFET™ III technology, which is specifically designed to minimize on-resistance and gate charge to provide superior switching performance.

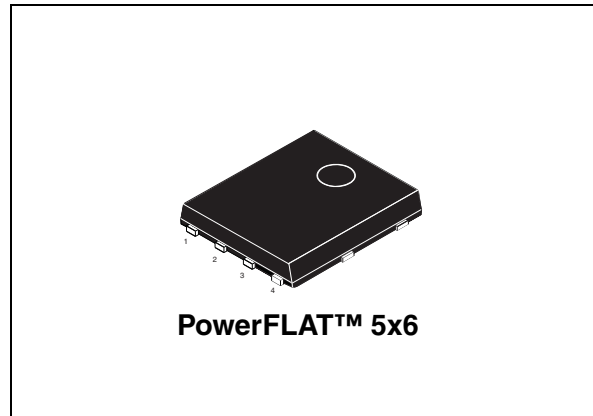


Figure 1. Internal schematic diagram

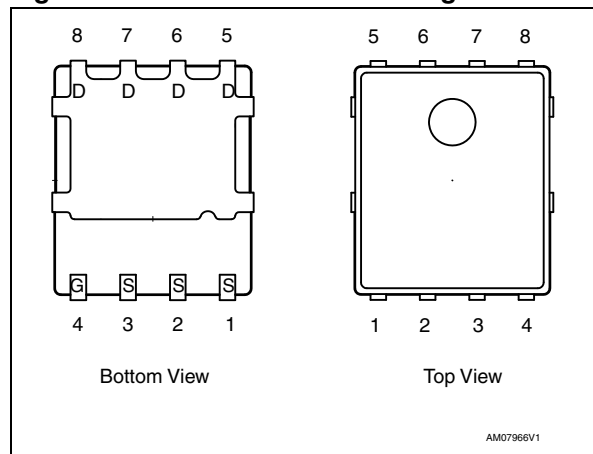


Table 1. Device summary

Order code	Marking	Package	Packaging
STL35N6F3	35N6F3	PowerFLAT™ 5x6	Tape and reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	60	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	35	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	25	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	10	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb}=100\text{ }^\circ\text{C}$	7	A
$I_{DM}^{(3)}$	Drain current (pulsed)	100	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	80	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	5	W
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. The value is rated according to R_{thj-c}
2. The value is rated according to $R_{thj-pcb}$
3. Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	31.3	$^\circ\text{C}/\text{W}$
$R_{thj-case}$	Thermal resistance junction-case max.	1.9	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1 inch², 2 oz Cu, $t < 10\text{ sec}$

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AV}	Not-repetitive avalanche current	5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AV}$, $V_{DD} = 50\text{ V}$)	409	mJ

2 Electrical characteristics

($T_J = 25\text{ °C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0$	60			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 60\text{ V}$, $V_{DS} = 60\text{ V}$, $T_C = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$		0.019	0.022	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	762	-	pF
C_{oss}	Output capacitance			173		pF
C_{rss}	Reverse transfer capacitance			16		pF
Q_g	Total gate charge	$V_{DD} = 30\text{ V}$, $I_D = 10\text{ A}$	-	13.6	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$		5.0		nC
Q_{gd}	Gate-drain charge (see Figure 13)			3.7		nC
R_g	Gate input resistance	$f = 1\text{ MHz}$ open drain	-	3.2	-	Ω

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD}=30\text{ V}$, $I_D=5\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 12)	-	9.7	-	ns
t_r	Rise time			2.9		ns
$t_{d(off)}$	Turn-off delay time			19		ns
t_f	Fall time			4		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		10	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		40	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=10\text{ A}$, $V_{GS}=0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD}=10\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=48\text{ V}$, $T_J=150\text{ }^\circ\text{C}$ (see Figure 14)	-	33		ns
Q_{rr}	Reverse recovery charge			51.2		nC
I_{RRM}	Reverse recovery current			3.1		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration= 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

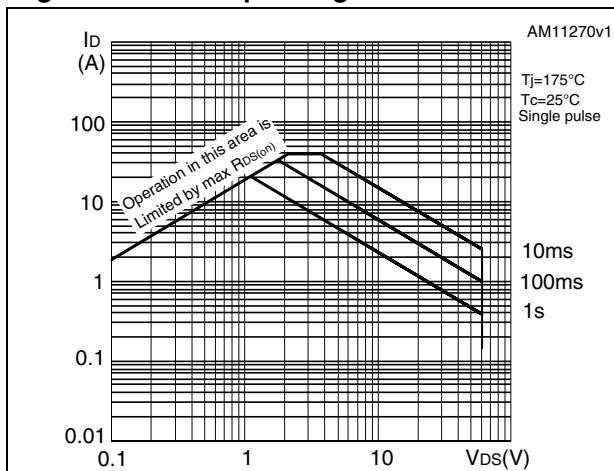


Figure 3. Thermal impedance

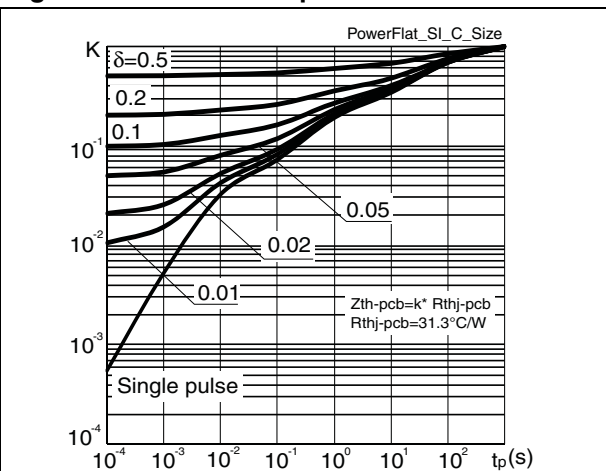


Figure 4. Output characteristics

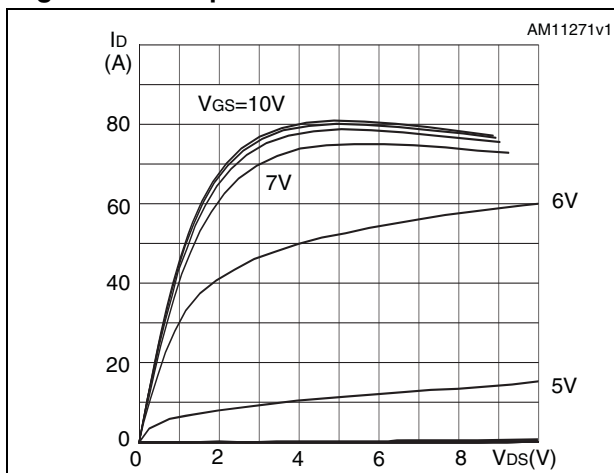


Figure 5. Transfer characteristics

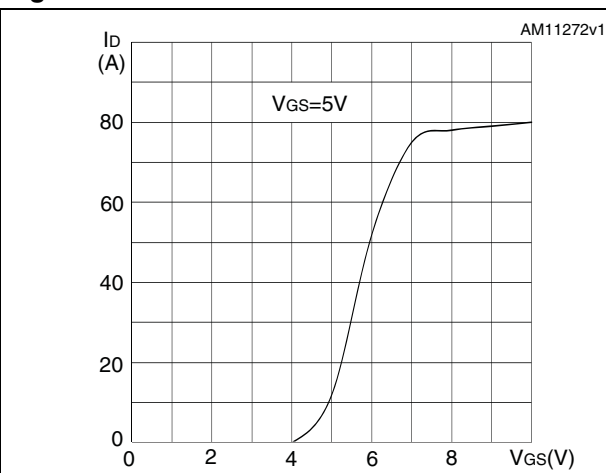


Figure 6. Normalized V_{DS} vs temperature

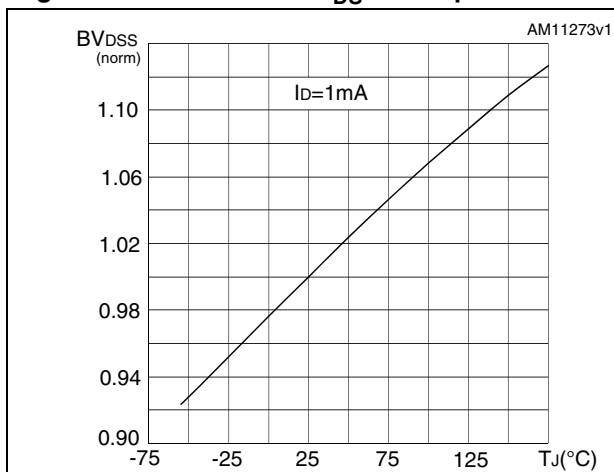


Figure 7. Static drain-source on-resistance

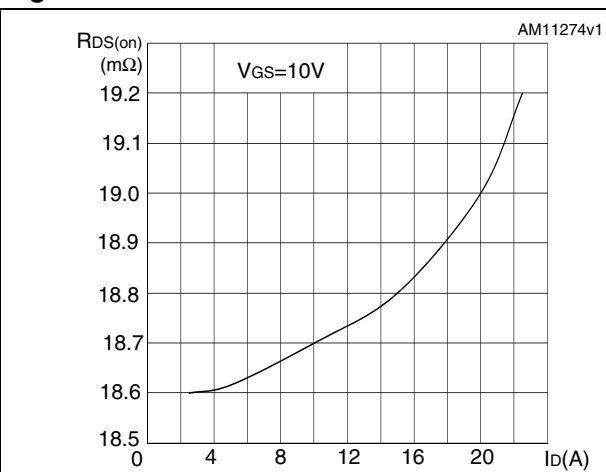


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

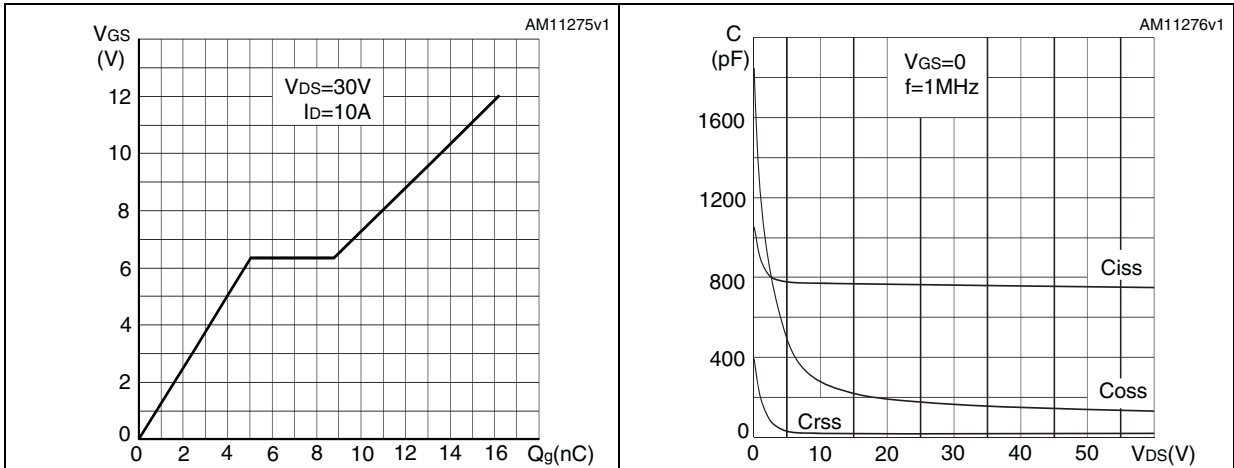
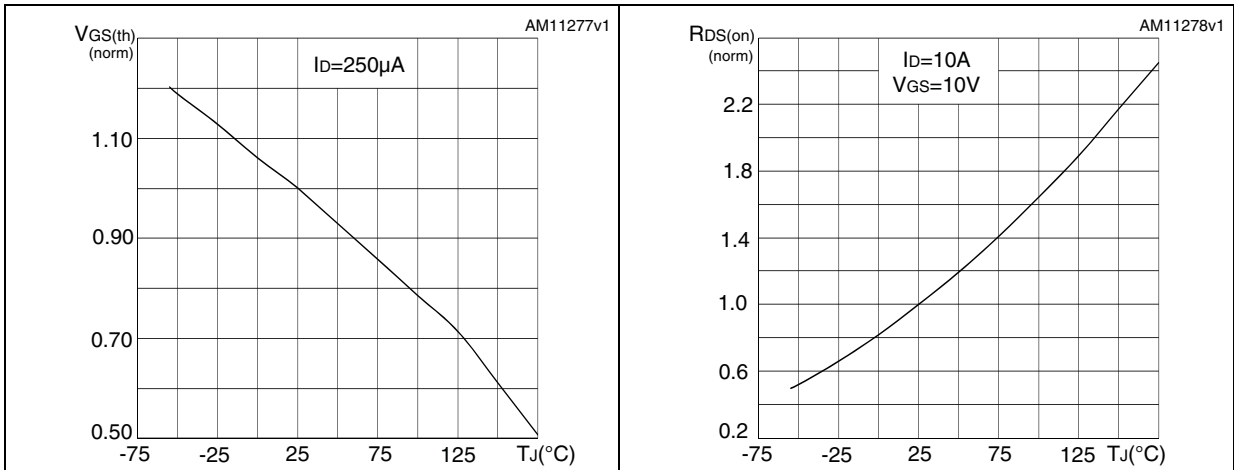


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on-resistance vs temperature



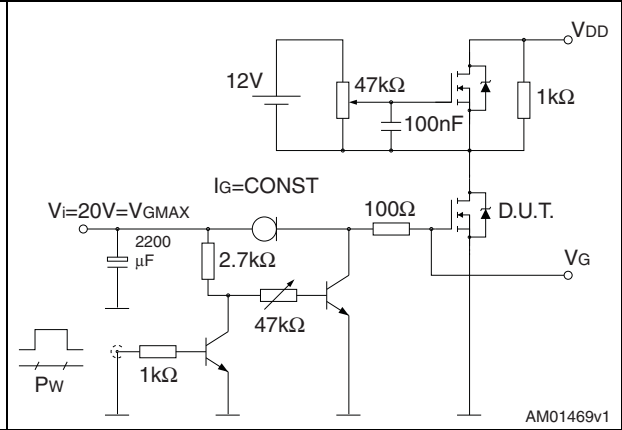
3 Test circuits

Figure 12. Switching times test circuit for resistive load



AM01468v1

Figure 13. Gate charge test circuit



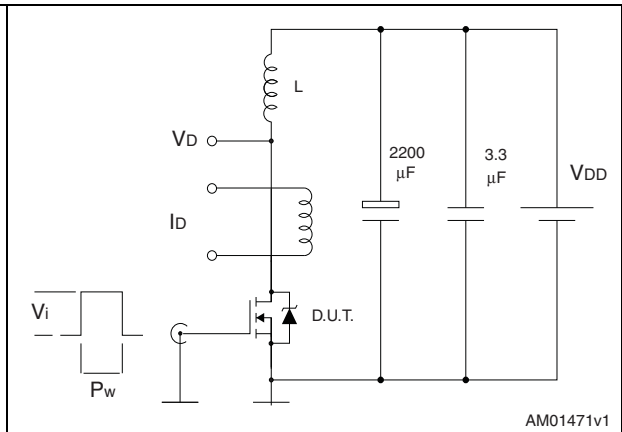
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Figure 14. Test circuit for inductive load switching and diode recovery times



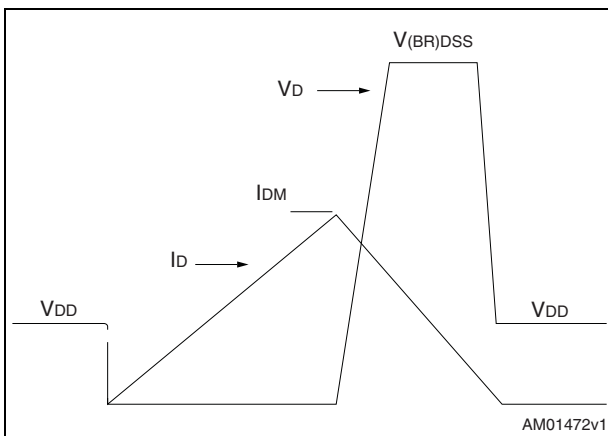
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Figure 15. Unclamped inductive load test circuit



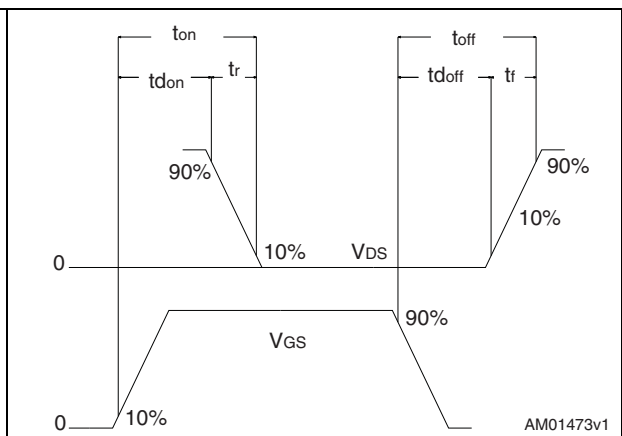
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Figure 16. Unclamped inductive waveform



AM01472v1

Figure 17. Switching time waveform



AM01473v1

4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. PowerFLAT™ 5x6 type C-B mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.83	0.93
A1	0	0.02	0.05
A3		0.20	
b	0.35	0.40	0.47
D		5.00	
D1		4.75	
D2	4.15	4.20	4.25
E		6.00	
E1		5.75	
E2	3.43	3.48	3.53
E4	2.58	2.63	2.68
e		1.27	
L	0.70	0.80	0.90

Figure 18. PowerFLAT™ 5x6 type C-B drawing

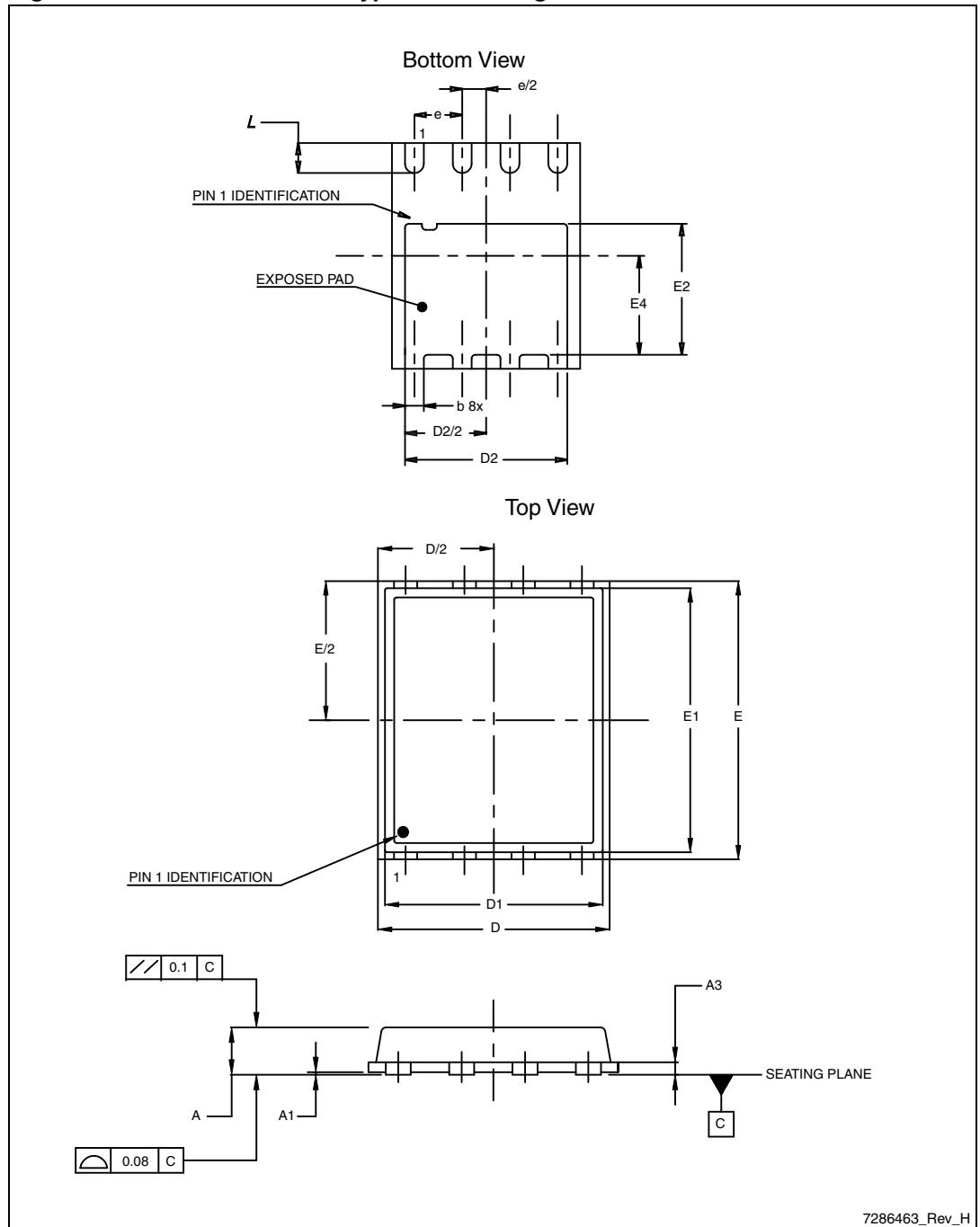


Table 10. PowerFLAT™ 5x6 type S-C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D		5.20	
E		6.15	
D2	4.11		4.31
E2	3.50		3.70
e		1.27	
e1		0.65	
L	0.715		1.015
K	1.05		1.35

Figure 19. PowerFLAT™ 5x6 type S-C mechanical data

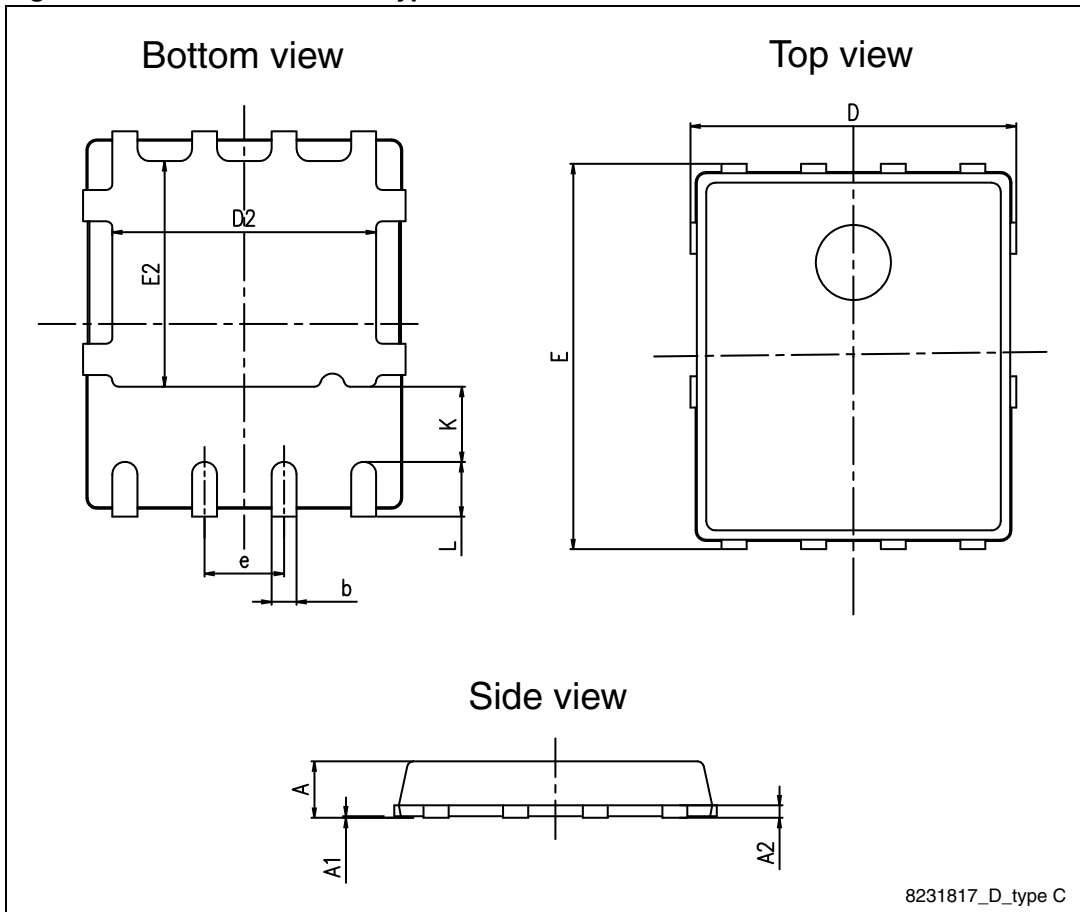
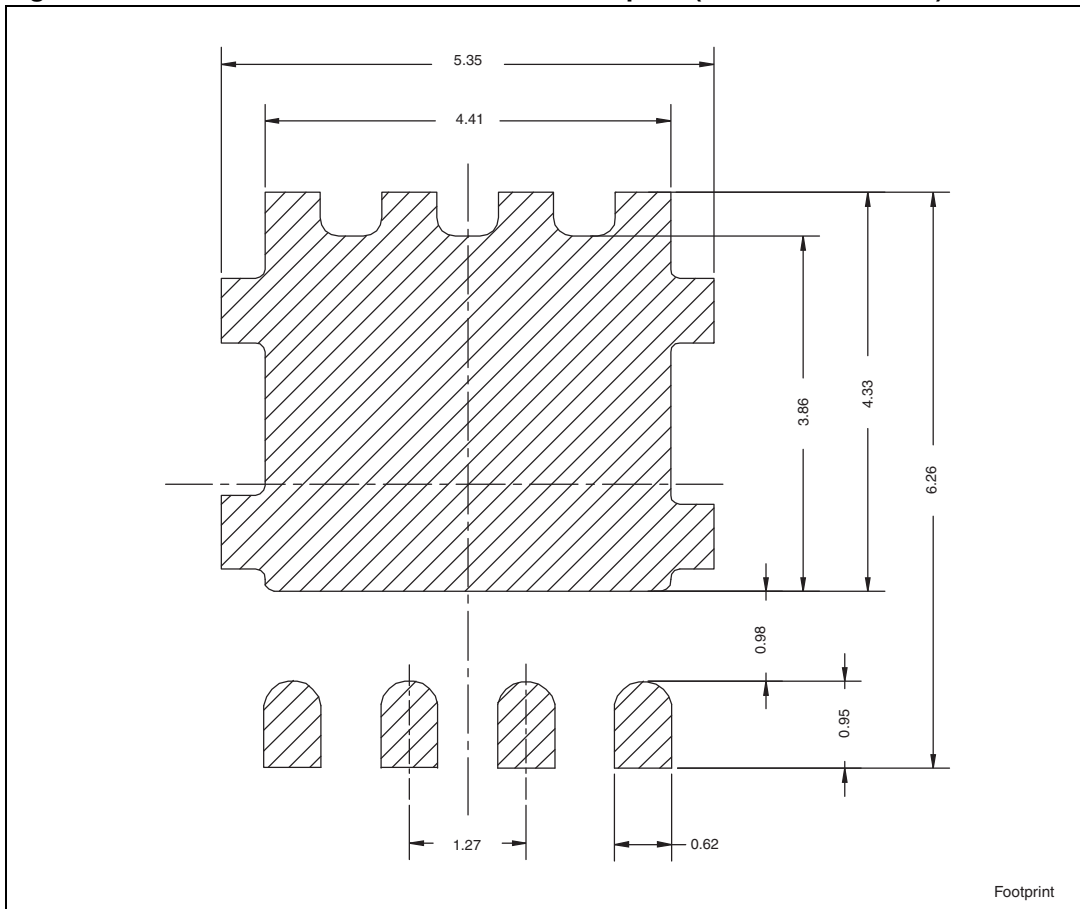


Figure 20. PowerFLAT™ 5x6 recommended footprint (dimensions in mm)



5 Packaging mechanical data

Figure 21. PowerFLAT™ 5x6 tape

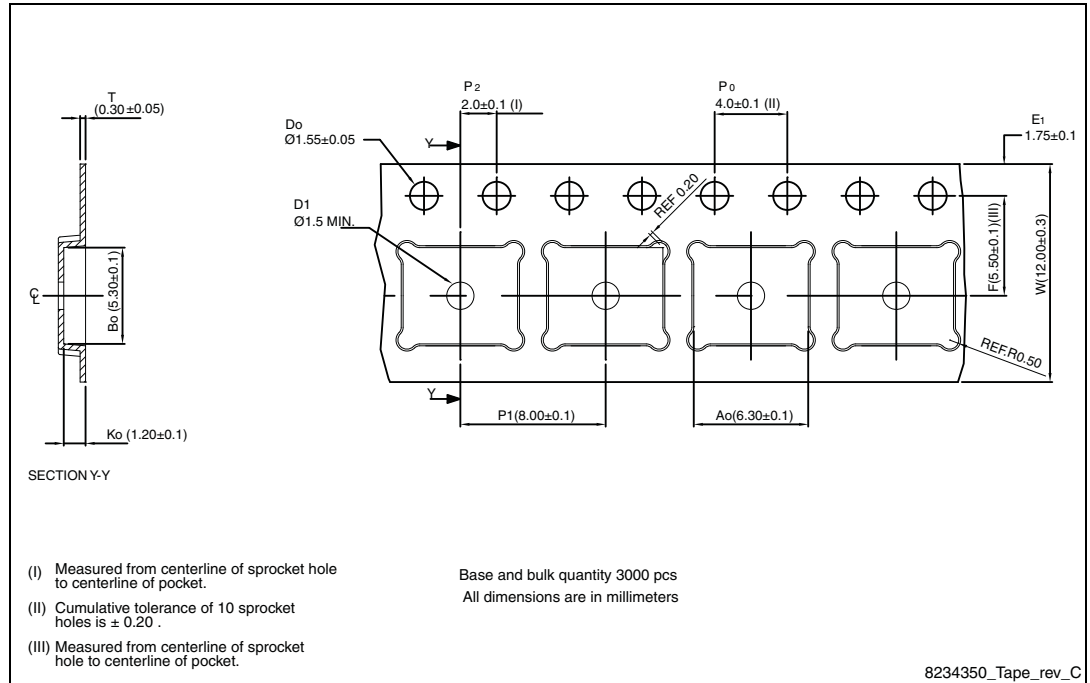


Figure 22. PowerFLAT™ 5x6 package orientation in carrier tape.

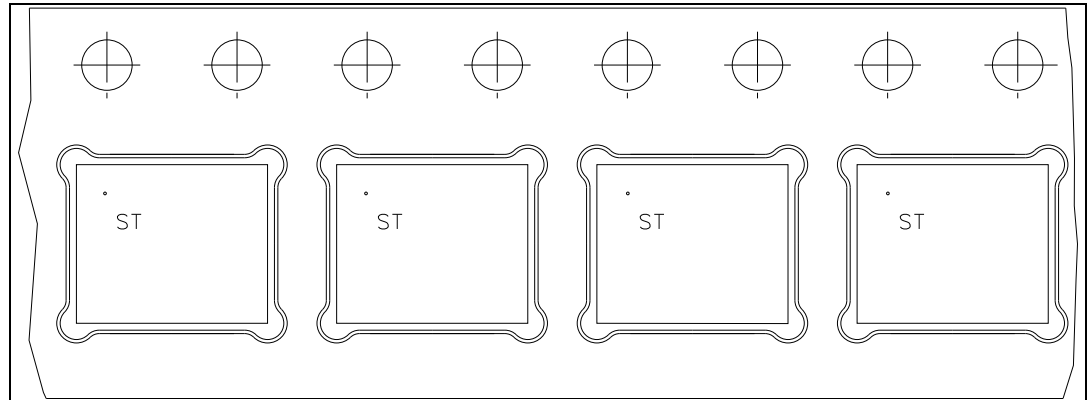
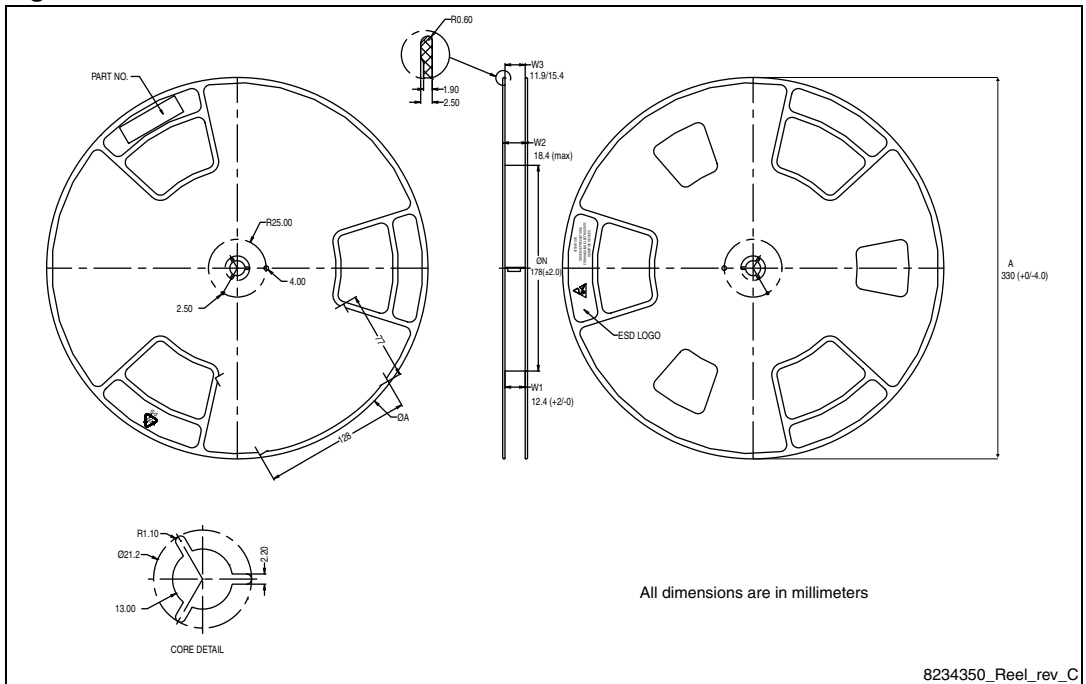


Figure 23. PowerFLAT™ 5x6 reel



6 Revision history

Table 11. Document revision history

Date	Revision	Changes
29-Oct-2009	1	First release.
15-Nov-2011	2	<i>Section 4: Package mechanical data</i> has been updated. Minor text changes. Document status promoted from preliminary data to datasheet.
27-Mar-2012	3	<i>Section 2.1: Electrical characteristics (curves)</i> has been inserted.
11-May-2012	4	<i>Figure 2: Safe operating area</i> and <i>Figure 3: Thermal impedance</i> have been changed.

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